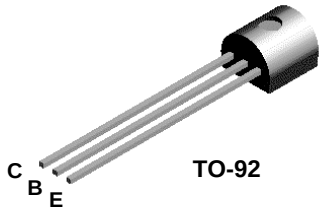
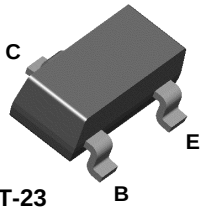
FAIRCHILD
SEMICONDUCTOR TM

2N5551



TO-92

MMBT5551



SOT-23
Mark: 3S

NPN General Purpose Amplifier

This device is designed for general purpose high voltage amplifiers and gas discharge display drivers.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	160	V
V_{CBO}	Collector-Base Voltage	180	V
V_{EBO}	Emitter-Base Voltage	6.0	V
I_C	Collector Current - Continuous	600	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:
1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		2N5551	*MMBT5551	
P_D	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

NPN General Purpose Amplifier
(continued)

Electrical Characteristics
TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHARACTERISTICS					
$V_{(BR)CEO}$	Collector-Emitter Sustaining Voltage*	I_C = 1.0 mA, I_B = 0	160		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C = 100 μA, I_E = 0	180		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E = 10 μA, I_C = 0	6.0		V
I_{CBO}	Collector Cutoff Current	V_{CB} = 120 V, I_E = 0, V_{CB} = 120 V, I_E = 0, T_A = 100°C		50 50	nA μA
I_{EBO}	Emitter Cutoff Current	V_{EB} = 4.0 V, I_C = 0		50	nA
ON CHARACTERISTICS					
h_{FE}	DC Current Gain	I_C = 1.0 mA, V_{CE} = 5.0 V I_C = 10 mA, V_{CE} = 5.0 V I_C = 50 mA, V_{CE} = 5.0 V	80 80 30	 250 	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C = 10 mA, I_B = 1.0 mA I_C = 50 mA, I_B = 5.0 mA		0.15 0.20	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C = 10 mA, I_B = 1.0 mA I_C = 50 mA, I_B = 5.0 mA		1.0 1.0	V V
SMALL SIGNAL CHARACTERISTICS					
f_T	Current Gain - Bandwidth Product	I_C = 10 mA, V_{CE} = 10 V, f = 100 MHz	100	300	MHz
C_{obo}	Output Capacitance	V_{CB} = 10 V, I_E = 0, f = 1.0 MHz		6.0	pF
C_{ibo}	Input Capacitance	V_{BE} = 0.5 V, I_C = 0, f = 1.0 MHz		20	pF
h_{fe}	Small-Signal Current Gain	I_C = 1.0 mA, V_{CE} = 10 V, f = 1.0 kHz	50	250	
NF	Noise Figure	I_C = 250 μA, V_{CE} = 5.0 V, R_S=1.0 kΩ, f=10 Hz to 15.7 kHz		8.0	dB

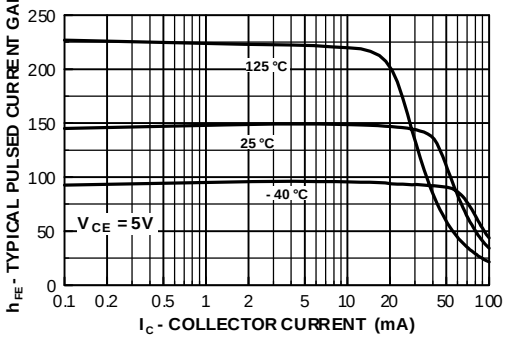
*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

Spice Model

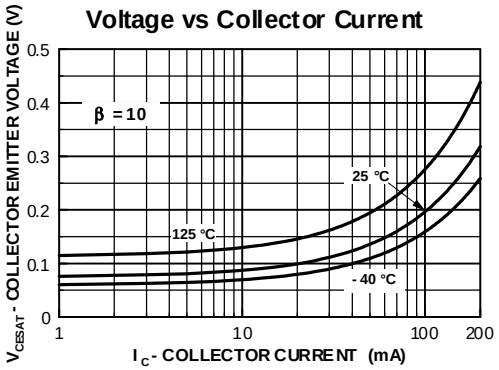
NPN (Is=2.511f Xti=3 Eg=1.11 Vaf=100 Bf=242.6 Ne=1.249 Ise=2.511f Ikf=.3458 Xtb=1.5 Br=3.197 Nc=2 Isc=0 Ikr=0 Rc=1 Cjc=4.883p Mjc=.3047 Vjc=.75 Fc=.5 Cje=18.79p Mje=.3416 Vje=.75 Tr=1.202n Tf=560p Itf=50m Vtf=5 Xtf=8 Rb=10)

Typical Characteristics

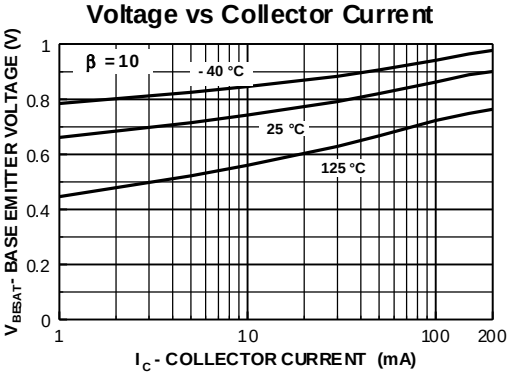
Typical Pulsed Current Gain vs Collector Current



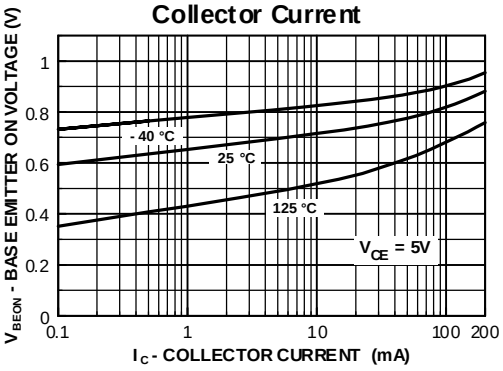
Collector-Emitter Saturation Voltage vs Collector Current



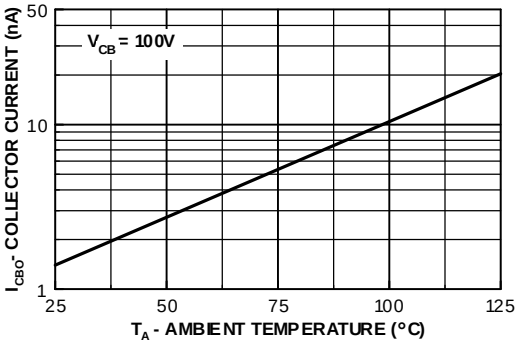
Base-Emitter Saturation Voltage vs Collector Current



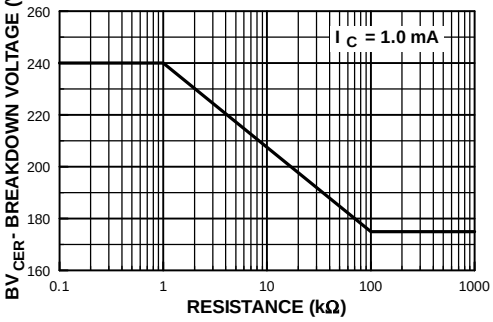
Base Emitter ON Voltage vs Collector Current



Collector-Cutoff Current vs. Ambient Temperature

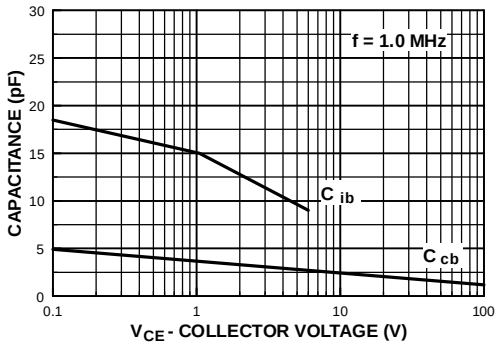


Collector-Emitter Breakdown Voltage with Resistance Between Emitter-Base

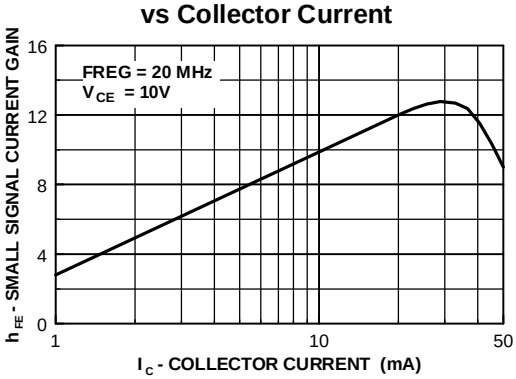


Typical Characteristics (continued)

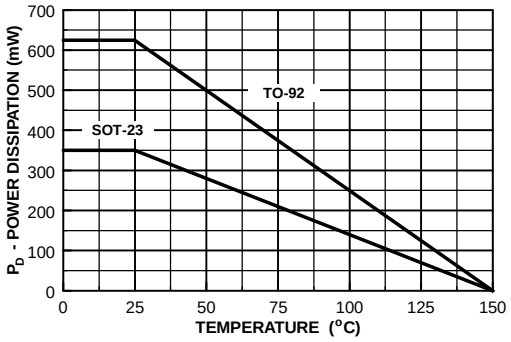
Input and Output Capacitance vs Reverse Voltage



Small Signal Current Gain vs Collector Current



Power Dissipation vs Ambient Temperature



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